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(56) Documents Cited:

US 5790461 A US 20150039547 A1 US 20140310220 A1

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(54) Title of the Invention: Memory cell structure Abstract Title: Memory cell structure

(57) A memory cell structure includes a synapse memory cell including plural cell components, each of the plural cell components including a unit cell, plural write lines arranged for writing a synapse state to the synapse memory cell, each of the plural write lines being used for writing one of a first set of a predetermined number of states to a corresponding cell component by writing one of a second set of the predetermined number of states to the unit cell included in the corresponding cell component, the first set depending on the second set and a number of the unit cell included in the corresponding cell component, and a read line arranged for reading the synapse state from the synapse memory cell, the read line being used for reading one of the first set of the predetermined number of states from all of the plural cell components simultaneously.



